

# MOS INTEGRATED CIRCUIT $\mu PD444008L$

# 4M-BIT CMOS FAST SRAM 512K-WORD BY 8-BIT

#### **Description**

The  $\mu$ PD444008L is a high speed, low power, 4,194,304 bits (524,288 words by 8 bits) CMOS static RAM.

Operating supply voltage is 3.3 V  $\pm$  0.3 V.

The  $\mu$ PD444008L is packaged in 36-pin PLASTIC SOJ.

#### **Features**

• 524,288 words by 8 bits organization

• Fast access time : 8, 10, 12, ns (MAX.)

- Output Enable input for easy application
- Single +3.3 V power supply

#### **Ordering Information**

Part number	Package	Access time	Access time Supply current	
		ns (MAX.)	At operating	At standby
μPD444008LLE-A8	36-pin PLASTIC SOJ	8	185	5
μPD444008LLE-A10	(10.16 mm (400))	10	165	
μPD44008LLE-A12		12	155	
μPD444008LLE-A8-A		8	185	
μPD444008LLE-A10-A		10	165	
μPD444008LLE-A12-A		12	155	

**Remark** Products with -A at the end of the part number are lead-free products.

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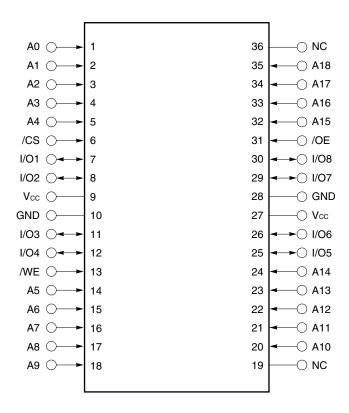
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#### Pin Configuration (Marking Side)

/xxx indicates active low signal.

36-pin PLASTIC SOJ (10.16 mm (400))



A0 - A18 : Address Inputs

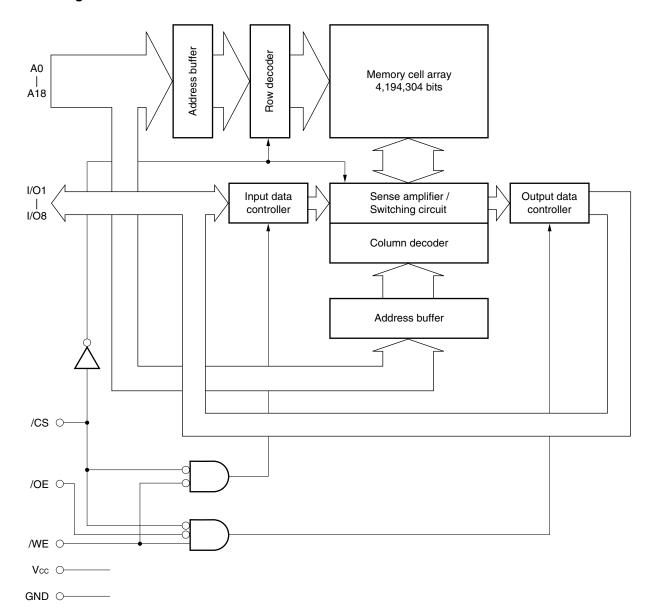
I/O1 - I/O8 : Data Inputs / Outputs

/CS : Chip Select
/WE : Write Enable
/OE : Output Enable
Vcc : Power supply
GND : Ground

NC : No connection

Remark Refer to Package Drawing for the 1-pin index mark.

## **Block Diagram**



**Truth Table** 

/CS	/OE	/WE	Mode	I/O	Supply current
Н	×	×	Not selected	High impedance	Isb
L	L	Н	Read	<b>D</b> оит	Icc
L	×	L	Write	Din	
L	Н	Н	Output disable	High impedance	

 $\textbf{Remark} \ \times : \ Don't \ care$ 

## **Electrical Specifications**

#### **Absolute Maximum Ratings**

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		-0.5 <sup>Note</sup> to +4.0	V
Input / Output voltage	VT		-0.5 <sup>Note</sup> to +4.0	V
Operating ambient temperature	TA		0 to 70	°C
Storage temperature	Tstg		-55 to +125	°C

Note -2.0 V (MIN.) (pulse width: 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

#### **Recommended Operating Conditions**

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	Vcc		3.0	3.3	3.6	V
High level input voltage	VIH		2.0		Vcc+0.3	V
Low level input voltage	VIL		-0.3 Note		+0.8	٧
Operating ambient temperature	TA		0		70	°C

Note -2.0 V (MIN.) (pulse width : 2 ns)



## DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test con	MIN.	TYP.	MAX.	Unit	
Input leakage current	lu	V <sub>IN</sub> = 0 V to V <sub>CC</sub>		-2		+2	μΑ
Output leakage current	ILO	V <sub>VO</sub> = 0 V to Vcc,		-2		+2	μΑ
		/CS = VIH or /OE = VIH	or /WE = V <sub>IL</sub>				
Operating supply current	Icc	/CS = V <sub>IL</sub> ,	Cycle time : 8 ns			185	mA
		I <sub>I/O</sub> = 0 mA,	Cycle time : 10 ns			165	
		Minimum cycle time	Cycle time : 12 ns			155	
Standby supply current	Isв	/CS = V <sub>IH</sub> , V <sub>IN</sub> = V <sub>IH</sub> or	VIL			40	mA
	I <sub>SB1</sub>	/CS ≥ Vcc - 0.2 V,				5	
		$V_{\text{IN}} \leq 0.2 \text{ V or } V_{\text{IN}} \geq V_{\text{CO}}$					
High level output voltage	Vон	Iон = -4.0 mA	2.4			٧	
Low level output voltage	Vol	I <sub>OL</sub> = +8.0 mA				0.4	٧

Remark VIN: Input voltage

VI/o : Input / Output voltage

## Capacitance (T<sub>A</sub> = 25 °C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	V <sub>IN</sub> = 0 V			6	pF
Input / Output capacitance	Ci/o	V <sub>I/O</sub> = 0 V			8	pF

Remarks 1. VIN: Input voltage

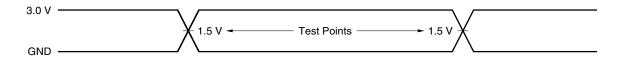
Vi/o : Input / Output voltage

 $\textbf{2.} \ \ \, \textbf{These parameters are periodically sampled and not 100\% tested}.$ 

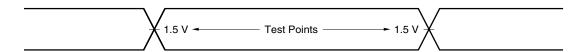
#### AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

#### **AC Test Conditions**

#### Input Waveform (Rise and Fall Time ≤ 3 ns)

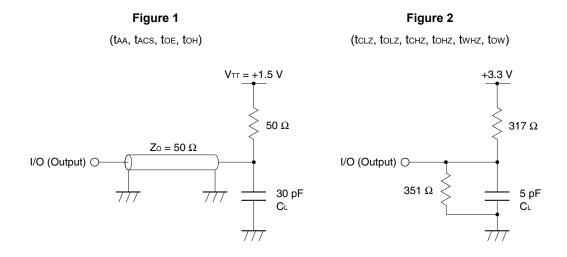


#### **Output Waveform**



#### **Output Load**

AC characteristics directed with the note should be measured with the output load shown in **Figure 1** or **Figure 2**.



Remark CL includes capacitances of the probe and jig, and stray capacitances.

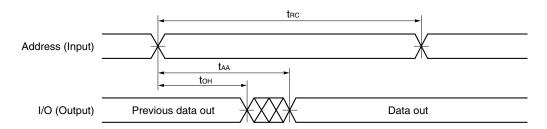
#### **Read Cycle**

Parameter	Symbol	-A8		-A10 -A1		12	Unit	Notes	
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	<b>t</b> RC	8		10		12		ns	
Address access time	taa		8		10		12	ns	1
/CS access time	tacs		8		10		12	ns	
/OE access time	<b>t</b> oe		4		5		6	ns	
Output hold from address change	<b>t</b> он	3		3		3		ns	
/CS to output in low impedance	tclz	3		3		3		ns	2, 3
/OE to output in low impedance	tolz	0		0		0		ns	
/CS to output in high impedance	<b>t</b> cHZ		4		5		6	ns	
/OE to output hold in high impedance	tонz		4		5		6	ns	

Notes 1. See the output load shown in Figure 1.

- 2. Transition is measured at  $\pm$  200 mV from steady-state voltage with the output load shown in **Figure 2**.
- **3.** These parameters are periodically sampled and not 100% tested.

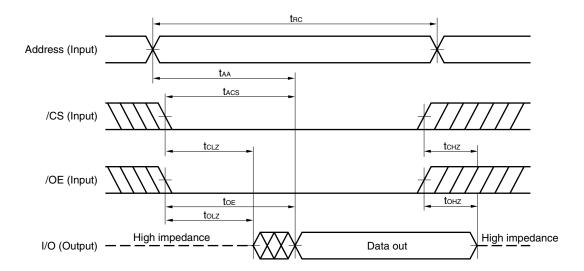
## Read Cycle Timing Chart 1 (Address Access)



Remarks 1. In read cycle, /WE should be fixed to high level.

2. /CS = /OE = VIL

## Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

**Remark** In read cycle, /WE should be fixed to high level.

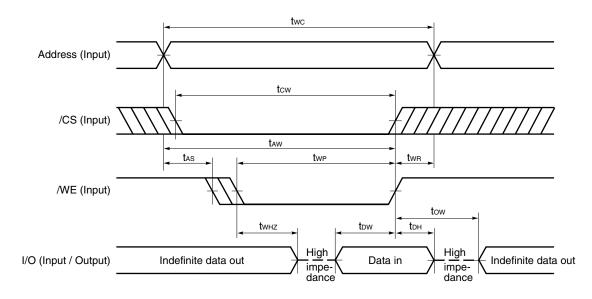
#### Write Cycle

Parameter	Symbol	-A8		-A10		-A12		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	8		10		12		ns	
/CS to end of write	tcw	6		7		8		ns	
Address valid to end of write	taw	6		7		8		ns	
Write pulse width	<b>t</b> wp	6		7		8		ns	
Data valid to end of write	<b>t</b> <sub>DW</sub>	4		5		6		ns	
Data hold time	<b>t</b> DH	0		0		0		ns	
Address setup time	<b>t</b> as	0		0		0		ns	
Write recovery time	twr	0		0		0		ns	
/WE to output in high impedance	<b>t</b> wHz		4		5		6	ns	1, 2
Output active from end of write	tow	3		3		3		ns	

**Notes 1.** Transition is measured at  $\pm$  200 mV from steady-state voltage with the output load shown in **Figure 2**.

2. These parameters are periodically sampled and not 100% tested.

#### Write Cycle Timing Chart 1 (/WE Controlled)



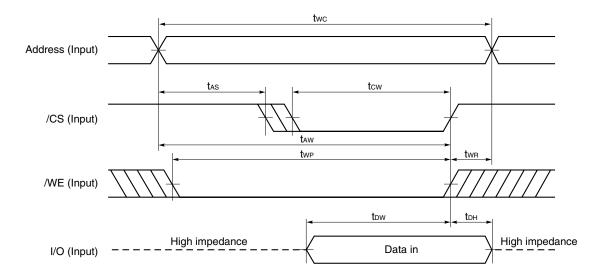
Cautions 1. /CS or /WE should be fixed to high level during address transition.

2. Do not input data to the I/O pins while they are in the output state.

Remarks 1. Write operation is done during the overlap time of a low level /CS and a low level /WE.

2. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.

## Write Cycle Timing Chart 2 (/CS Controlled)



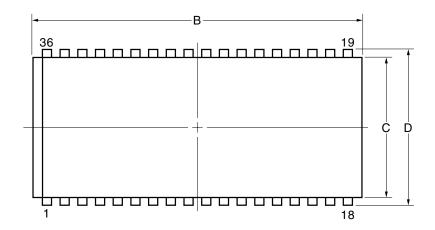
Cautions 1. /CS or /WE should be fixed to high level during address transition.

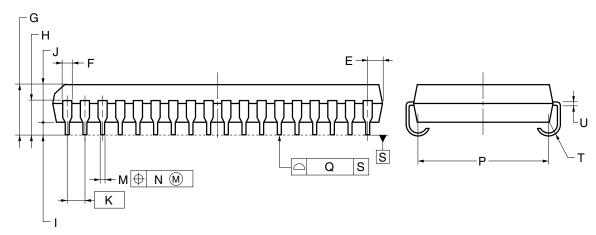
2. Do not input data to the I/O pins while they are in the output state.

**Remark** Write operation is done during the overlap time of a low level /CS and a low level /WE.

## **Package Drawing**

## 36-PIN PLASTIC SOJ (10.16 mm (400))





#### NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
В	23.6±0.20
С	10.16±0.1
D	11.18±0.2
Е	1.005±0.1
F	0.74
G	3.5±0.2
Н	2.545±0.2
ı	0.8 MIN.
J	2.6
K	1.27 (T.P.)
М	$0.42^{+0.08}_{-0.07}$
N	0.12
Р	9.4±0.20
Q	0.1
Т	R 0.85
U	$0.22^{+0.08}_{-0.07}$
	P36LE-400A-2

## **Recommended Soldering Conditions**

Please consult with our sales offices for soldering conditions of the  $\mu PD444008L$ .

## **Type of Surface Mount Device**

 $\mu$ PD444008LLE : 36-pin PLASTIC SOJ (10.16 mm (400))  $\mu$ PD444008LLE-A : 36-pin PLASTIC SOJ (10.16 mm (400))

## <R> Quality Grade

- A quality grade of the products is "Standard".
- Anti-radioactive design is not implemented in the products.
- Semiconductor devices have the possibility of unexpected defects by affection of cosmic ray that reach to the ground and so forth.

## **Revision History**

Edition/	Pa	Page Type of		Location	Description
Date	This Previous		revision		(Previous edition $ o$ This edition)
	edition	edition			
6th edition/	p.12	p.12	Addition	Quality Grade	Section of Quality Grade has been added.
Sep. 2006					

NEC  $\mu$ PD444008L

[MEMO]

#### NOTES FOR CMOS DEVICES —

#### (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between  $V_{\rm IL}$  (MAX) and  $V_{\rm IH}$  (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between  $V_{\rm IL}$  (MAX) and  $V_{\rm IH}$  (MIN).

#### (2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

#### ③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

#### **4** STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

#### (5) POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

#### 6 INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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